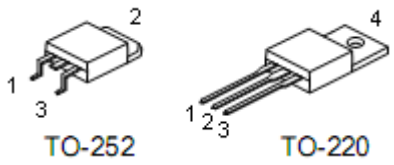
1. Description

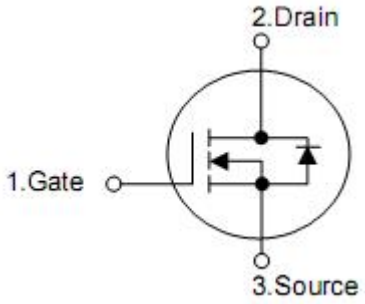
This Power MOSFET is produced using KIA`s advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

2. Features

- $R_{DS(ON)}$=0.38Ω@V_{GS}=10V.
- Low gate charge (typical 15nC)
- High ruggedness
- Fast switching capability
- Avalanche energy specified
- Improved dv/dt capability

3. Pin configuration





Pin	Function
1	Gate
2	Drain
3	Source
4	Drain

4. Absolute maximum ratings

(T_C= 25ºC, unless otherwise noted)

Parameter		Symbol	Rating		Units
			TO-220	TO-252	
Drain-source voltage		V_{DSS}	350		V
Gate-source voltage		V_{GSS}	±20		V
Drain current continuous	T_C=25ºC	I_D	11	11*	A
	T_C=100ºC		6.6	6.6*	A
Drain current pulsed (note1)		I_{DM}	36		A
Avalanche Enlsed	Repetitive (note1)	E_{AR}	9.91		mJ
	Single pulse (note2)	E_{AS}	423		mJ
Avalanche current (note 1)		I_{AR}	9.0		A
Peak diode recovery dv/dt (note3)		dv/dt	4.5		V/ns
Total power dissipation	T_C=25ºC	P_D	99		W
	Derate above 25ºC		0.79		W/ ºC
Operating and storage temperature range		T_J, T_{STG}	-55~+150		ºC
Maximum lead temperature for soldering Purposes,1/8`` form case for 5 seconds		T_L	300		ºC

*Drain current limited by maximum junction temperature.

5. Thermal characteristics

Parameter	Symbol	Rating	Unit
Thermal resistance,Junction-amient	R_{thJA}	62.5	ºC/W
Thermal resistance,case-to-sink typ.	R_{thJS}	0.5	ºC/W
Thermal resistance,Junction-case	R_{thJC}	1.26	ºC/W

6. Electrical characteristics

(T_C= 25 ºC, unless otherwise noted)

Parameter		Symbol	Test conditions	Min	Typ	Max	Unit
Off characteristics							
Drain-source breakdown voltage		BV_{DSS}	V_{GS}=0V,I_D=250μA	350	-	-	V
Zero gate voltage drain current		I_{DSS}	V_{DS}=350V, V_{GS}=0V	-	-	1	μA
			V_{DS}=280V, T_C=125ºC	-	-	10	μA
Gate-body leakage current	Forward	I_{GSS}	V_{GS}=20V, V_{DS}=0V	-	-	10	uA
	Reverse		V_{GS}=-20V,V_{DS}=0V	-	-	-10	uA
Breakdown voltage temperature coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D=250μA	-	0.35	-	V/ ºC
On characteristics							
Gate threshold voltage		$V_{GS(TH)}$	V_{DS}= V_{GS} I_D=250μA	2.0	-	4.0	V
Static drain-source on- resistance		$R_{DS(ON)}$	V_{DS}=10V,I_D=4.5A	-	0.38	0.48	Ω
Forward transconductance		g_{FS}	V_{DS}=40V,I_D=4.5A(note4)	-	7.8	-	S
Dynamic characteristics							
Input capacitance		C_{ISS}	V_{DS}=25V,V_{GS}=0V, f=1MHz	-	844	-	pF
Output capacitance		C_{OSS}		-	162	-	pF
Reverse transfer capacitance		C_{RSS}		-	4	-	pF
Switching characteristics							
Turn-on delay time		$t_{D(ON)}$	V_{DD}=175V,I_D=9.0A, R_G=25Ω (note4,5)	-	25	-	ns
Rise time		t_R		-	23.5	-	ns
Turn-off delay time		$t_{D(OFF)}$		-	77	-	ns
Fall time		t_F		-	47.5	-	ns
Total gate charge		Q_G	V_{DS}=280V,I_D=9.0A V_{GS}=10V (note4,5)	-	15	-	nC
Gate-source charge		Q_{GS}		-	4	-	nC
Gate-drain charge		Q_{GD}		-	5	-	nC
Drain-source diode characteristics							
drain-source diode forward voltage		V_{SD}	V_{GS}=0V,I_{SD}=11A	-	-	1.4	V
Continuous drain-source current		I_S		-	-	11	A
Pulsed drain-source current		I_{SM*}				36	A
Reverse recovery time		t_{RR}	I_S=9.0A dI$_{SD}$/dt=100A/μs (note4)		317	-	ns
Reverse recovery charge		Q_{RR}			2.5	-	μC

Notes:1.repetitive rating:pulse width limited by maximum junction temperature

2.L=6.3mH,I_{AS}=9.0A,V_{DD}=50V,R_G=25Ω,starting T_J=25ºC

3.I_{SD}≤11A,di/dt≤100A/μs,V_{DD}≤BV_{DSS},starting T_J=25ºC

4.Pulse test:pulse width≤300μs,duty cycle≤2%

5.Essentially independent of operating temperature

7. Typical characteristics

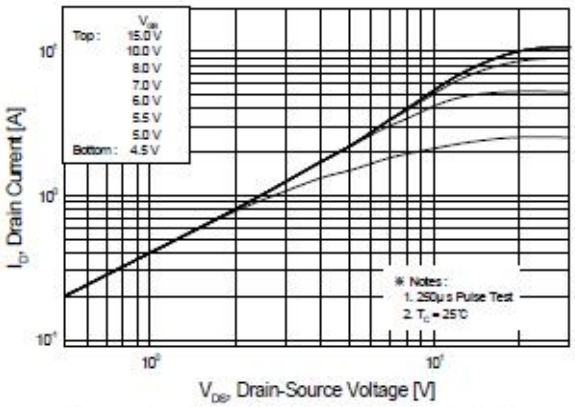


Figure 1. On-Region Characteristics

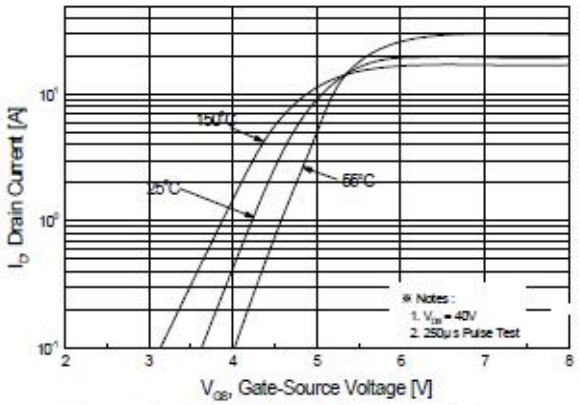


Figure 2. Transfer Characteristics

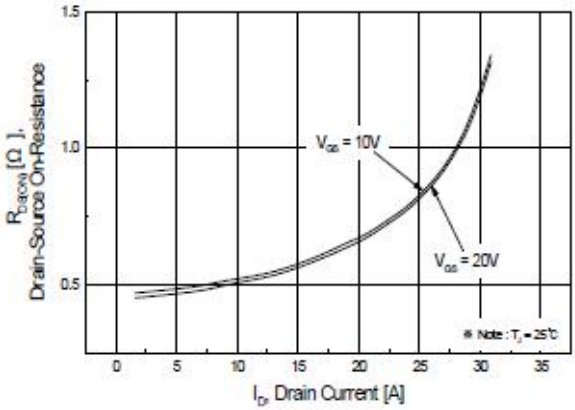


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

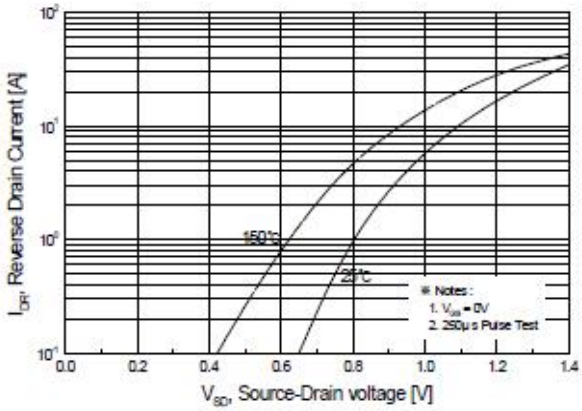


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

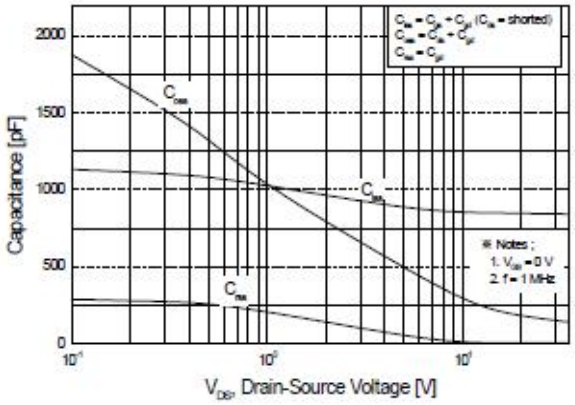


Figure 5. Capacitance Characteristics

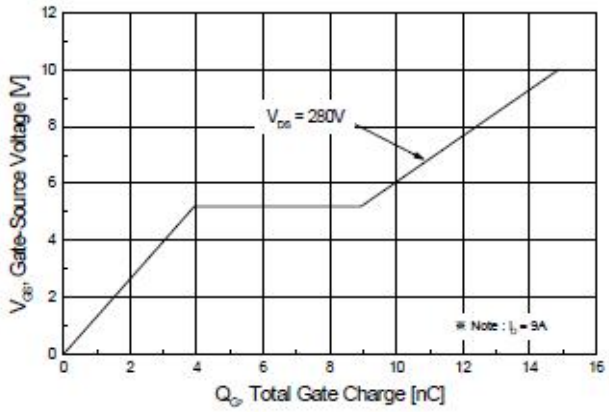


Figure 6. Gate Charge Characteristics

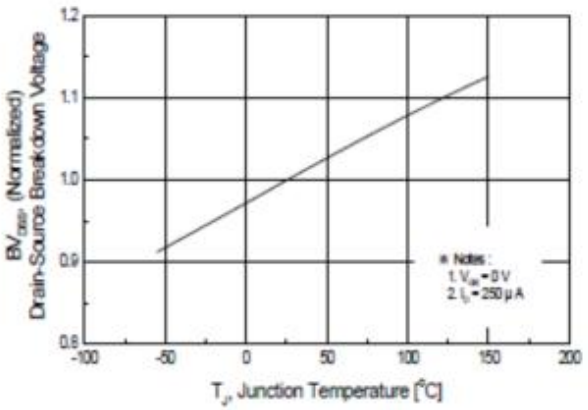


Figure 7. Breakdown Voltage Variation vs Temperature

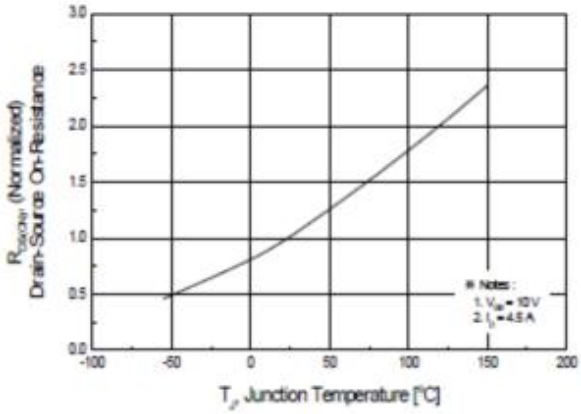


Figure 8. On-Resistance Variation vs Temperature

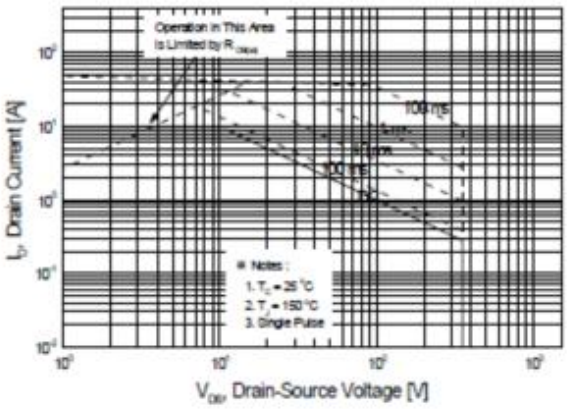


Figure 9. Maximum Safe Operating Area

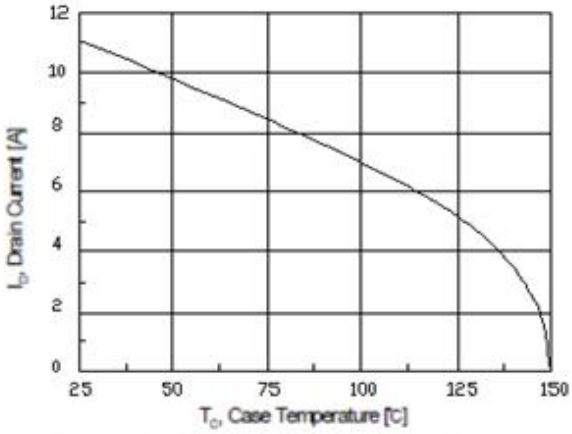


Figure 10. Maximum Drain Current vs Case Temperature

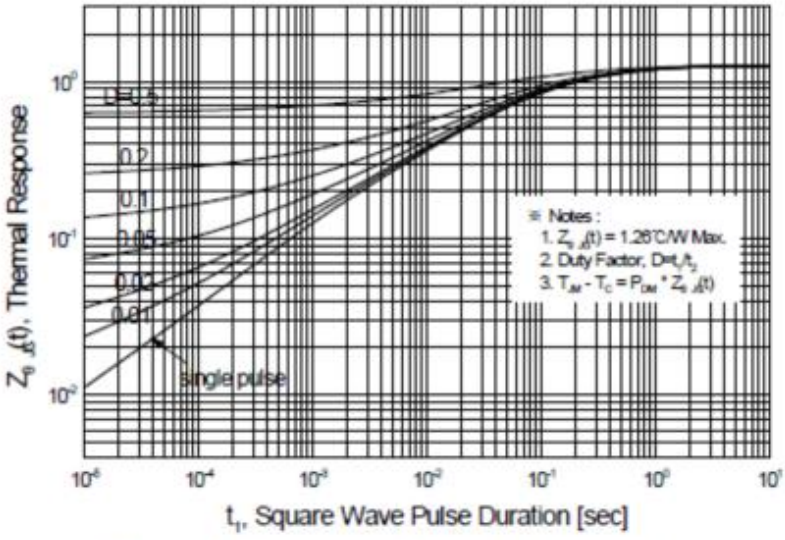


Figure 11. Transient Thermal Response Curve

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by KIA ***manufacturer:***

Other Similar products are found below :

614233C 648584F FDPF9N50NZ IRFD120 IRFF430 JANTX2N5237 2N7000 FCA20N60_F109 FDZ595PZ 2SK2267(Q) 2SK2545(Q,T) 405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C PSMN4R2-30MLD TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6 C3M0021120D DMN13M9UCA6-7 BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IPS60R1K0PFD7SAKMA1 IPS60R360PFD7SAKMA1 IPS60R600PFD7SAKMA1 IPS60R210PFD7SAKMA1 DMN2990UFB-7B